

## 2N3055C

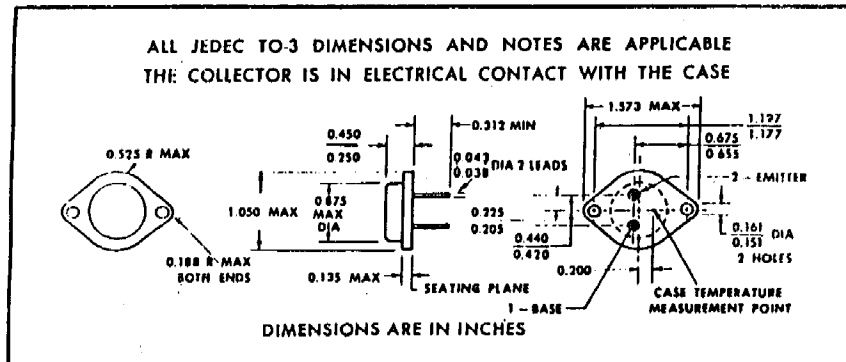
### N-P-N SILICON POWER TRANSISTOR

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^\circ C$  unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{CEV}$ Collector cutoff current ( $V_{BE} = -1.5 V$ )	$V_{CE} = 80V$ $V_{CE} = 80V$ $T_{case} = 150^\circ C$			5	mA
				30	mA
$I_{CEO}$ Collector cutoff current ( $I_B = 0$ )	$V_{CE} = 30V$		0.7		mA
$I_{EBO}$ Emitter cutoff current ( $I_C = 0$ )	$V_{EB} = 7 V$		1		mA
$V_{CEV(sus)}^*$ Collector-emitter sustaining voltage ( $V_{BE} = -1.5V$ )	$I_C = 100mA$	70			V
$V_{CEO(sus)}^*$ Collector-emitter sustaining voltage ( $I_B = 0$ )	$I_C = 200mA$	60			V
$V_{CE(sat)}^*$ Collector-emitter saturation voltage	$I_C = 4 A$ $I_B = 400mA$			1	V
				3	V
$V_{BE}^*$ Base-emitter voltage	$I_C = 4 A$ $V_{CE} = 4 V$		1.5		V

**ABSOLUTE MAXIMUM RATINGS**

$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	80V
$V_{CEV}$	Collector-emitter voltage ( $V_{BE} = -1.5 V$ )	70V
$V_{CER}$	Collector-emitter voltage ( $R_{BE} \leq 100 \Omega$ )	—
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	60V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	7V
$I_C$	Collector current	15A
$I_B$	Base current	7A
$P_{tot}$	Total power dissipation at $T_{case} \leq 25^\circ C$	115W
$T_{stg}$	Storage temperature	-65 to 200 °C
$T_J$	Junction temperature	200 °C



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